

# Simulated performance of a contrast-enhancement mat

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#	ARTICLE	IF	CITATIONS
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2	Advanced Topics In Lithography Modeling. Proceedings of SPIE, 1986, 0631, 276.	0.8	11
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4	The simulation of contrast-enhanced lithography. Microelectronic Engineering, 1991, 14, 299-309.	2.4	1
5	The modelling and simulation of nonlinear photobleaching materials. Microelectronic Engineering, 1991, 13, 493-496.	2.4	0
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